



## TO-92 Plastic-Encapsulate Transistors (PNP)

A1015

### A1015 TRANSISTOR (PNP)

#### FEATURES

Power dissipation

$P_{CM}$ : 0.4 W (Tamb=25°C)

Collector current

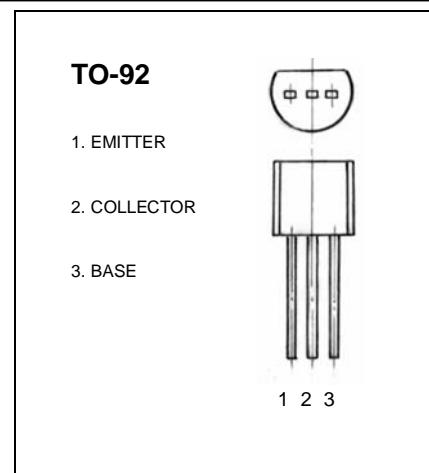
$I_{CM}$ : -0.15 A

Collector-base voltage

$V_{(BR)CBO}$ : -50 V

Operating and storage junction temperature range

$T_J, T_{stg}$ : -55°C to +150°C



#### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	$I_C = -100\mu A, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	$I_C = -0.1mA, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -50V, I_E = 0$			-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$			-0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE} = -6V, I_C = -2mA$	70		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100mA, I_B = -10mA$			-1.1	V
Transition frequency	$f_T$	$V_{CE} = -10V, I_C = -1mA$ $f = 30MHz$	80			MHz

#### CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y	GR
Range	70-140	120-240	200-400